Symmetrical Gate Turn-Off Thyristor Type SA25AP1200FT



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Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	2500	V
V_{RSM}	Non-repetitive peak off-state voltage, (note 1)	2600	V
V _{RRM}	Repetitive peak reverse voltage	375	V
V_{RSM}	Non-repetitive peak reverse voltage	375	V
note 1)	V _{GK} = −2V		

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I _{TGQ}	Peak turn-off current (note 1)	1200	А
L _S	Snubber loop impedance, $I_{TM} = I_{TGQ}$ (note 1)	0.3	nH
I _{T(AV)M}	Mean on-state current, T _{sink} = 55°C, (note 2)	790	Α
I _{T(RMS)}	Nominal RMS on-state current, T _{sink} = 25°C (note 2)	1600	Α
I _{TSM}	Peak non-repetitive surge current t _p = 10ms	13.0	kA
I _{TSM2}	Peak non-repetitive surge current (note 3)	23.0	kA
l ² t	I^2 t capacity for fusing $t_p = 10$ ms	840 · 10 ³	A^2s
(di/dt) _{cr}	Critical rate of rise of on-state current, (note 4)	1000	A/µs
P _{FGM}	Peak forward gate power	200	W
P_{RGM}	Peark reverse gate power	8	kW
I _{FGM}	Peak forward gate current	140	Α
V_{RGM}	Peak reverse gate voltage (note 5)	18	V
t _{off}	Minimum permissible off-time, $I_{TM} = I_{TGQ}$ (note 1)	80	μs
t _{on}	Minimum permissible off-time	20	μs
T _{jop}	Operating temperature range	-40 to +125	°C
T _{stg}	Storage temperature range	-40 to +150	°C
note 1)	T_j = 125°C, V_D = 80% V_{DM} , $V_{DM} \le V_{DRM}$, di_{GQ}/dt = 20A/ μ s, I_{TM} = I_{TGQ} and C_S =	= 3µF	
note 2)	Double-side cooled, single phase, 50Hz, 180° half-sinewave.		
note 3)	Half-sinewave, t _p = 2ms		
note 4)	For di/dt > 1000A/µs please consult factory.		
note 5)	May exceed this value during turn-off avalanche period.		



Characteristics

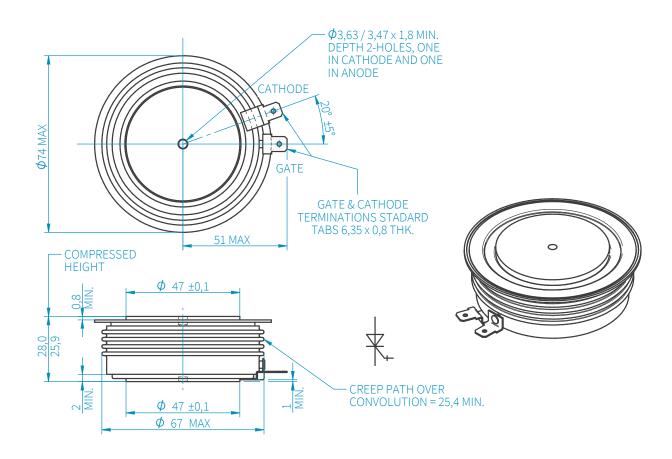
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_{TM}	Maximum peak on-state voltage	peak on-state voltage $I_G = 2A$, $I_T = 1200A$		2.4	2.7	V
IL	Latching current	T 25°C	-	10	-	А
I _H	Holding current	T _j = 25°C	-	10	-	А
(dv/dt) _{cr}	Critical rate of rise of off-state voltage	$V_{D} = 80\%V_{DRM}, V_{GR} = -2V$	1000	-	-	V/µs
I _{DRM}	Peak off-state current	Rated V_{DRM} , $V_{GR} = -2V$	-	-	50	mA
I _{RRM}	Peak reverse current	Rated V _{RRM}	-	-	100	mA
I_{GKM}	Peak negative gate leakage current	$V_{GR} = -16V$	-	-	200	mA
		$T_j = -40$ °C, $V_D = 25V$, $R_L = 25m\Omega$	-	1.0	-	V
V_{GT}	Gate trigger voltage	$T_j = 25^{\circ}C, V_D = 25V, R_L = 25m\Omega$	-	0.9	-	V
		$T_j = 125^{\circ}C, V_D = 25V, R_L = 25m\Omega$	-	0.8	-	V
		$T_j = -40$ °C, $V_D = 25V$, $R_L = 25m\Omega$	-	2	7	А
I_{GT}	Gate trigger current	$T_j = 25^{\circ}C, V_D = 25V, R_L = 25m\Omega$	-	0.5	2	А
		$T_j = 125^{\circ}\text{C}, V_D = 25\text{V}, R_L = 25\text{m}\Omega$	-	50	300	mA
t_d	Delay time	(note 2)	-	1.5	-	μs
t _{gt}	Turn-on time	Conditions as for t_d , (10% I_{GM} to 10% V_D	-	4.5	8.0	μs
t _f	Fall time	(note 3)	-	1	-	μs
t _{gq}	Turn-off time	Conditions as for t_f , (10% I_{GQ} to 10% I_{TGQ}	-	19	22	μs
I_{GQ}	Turn-off gate current	Conditions as for t _f	-	300	-	А
Q_{GQ}	Turn-off gate charge	Conditions as for t _f	-	4000	5000	mC
t _{tail}	Tail time	Conditions as for t_f , (10% I_{TGQ} to I_{TGQ} < 1A	-	50	75	μs
t _{gw}	Gate off-time (note 4)	Conditions as for t _f	150	-	-	μs
		Double side cooled	-	-	0.027	kW
R_{thJK}	Thermal resistance, junction to sink	Cathode side cooled	-	-	0.070	kW
		Anode side cooled	-	-	0.045	kW
F	Mounting force	(note 5)	15	-	25	kN
W _t	Weight		-	480	-	g
note 1)	Unless otherwise indicated T _j = 125°C					
note 2)	$V_D = 50\% V_{DRM}$, $I_{TGQ} = 1200A$, $I_{GM} = 20A$, $di_G/dt = 10A/\mu s$, $T_j = 25^{\circ}C$, $di/dt = 300A/\mu s$, $(10\% I_{GM} to 90\% V_D)$					
note 3)	$V_D = 80\% V_{DRM}$, $I_{TGQ} = 1200A$, $C_S = 3\mu F$, $di_G/dt = 20A/\mu s$, $V_{GR} = -16V$, $(90\% I_{TGQ})$					
note 4)	The gate off-time is the period during which the gate circuit is required to remain low impedance to allow for the passage of tail current.					
note 5)	For other clamping forces, consult factory.					

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